

**RELIABILITY MONITOR REPORT
FOR**

0.6 μ m Process

Dallas Semiconductor

**4401 South Beltwood Parkway
Dallas, TX 75244-3292**

**This Report was prepared by
Dallas Semiconductor Reliability Engineering**

Summary:

The data in the tables that follow was generated as the result of an on-going Process Reliability Monitor. The products covered by this process monitor are:

DS1002	DS1050	DS1052	DS1077	DS1077L
DS1085	DS1085L	DS1086	DS1086H	DS1086L
DS1087L	DS1094L	DS1099	DS1100	DS1100L
DS1102L	DS1110	DS1110L	DS1135	DS1135L
DS12885	DS12R885	DS12R885-5	DS1311	DS1318
DS1337	DS1337C	DS1338	DS1338-3	DS1338-33
DS1338C	DS1339	DS1339C	DS1339U-3	DS1339U-33
DS1340	DS1340C	DS1371	DS1374	DS1374-3
DS1374-33	DS1374C	DS1375	DS1390	DS1391
DS1392	DS1393	DS1482	DS1500	DS1501
DS1543	DS1553	DS1558	DS1615	DS1616
DS1620	DS1621	DS1626	DS1631	DS1631A
DS1643	DS1672	DS1678	DS1679	DS1682
DS1721	DS1722	DS1726	DS1731	DS1743
DS1748	DS1775	DS1805	DS1809	DS1820B
DS1822	DS1830	DS1831	DS1845	DS1846
DS1849	DS1851	DS1854	DS1855	DS1858
DS1870	DS1921	DS1921G	DS1921H	DS1921Z
DS1961	DS2030	DS2045	DS2117M	DS2118M
DS2119M	DS2120	DS2125	DS2127	DS2129
DS21349	DS21352	DS21354	DS21448	DS2148
DS2149	DS21552	DS21554	DS21600	DS21602
DS21604	DS21610	DS2196	DS2197	DS21Q352
DS21Q354	DS21Q43	DS21Q50	DS21Q552	DS21Q554
DS21Q58	DS21Q59	DS2401	DS2405	DS2408
DS2409	DS2411	DS2415	DS2417	DS2421
DS2422	DS2432	DS2433	DS2436	DS2438
DS2450	DS2470	DS2490	DS2501	DS2502
DS2503	DS2505	DS2702	DS2720	DS2740
DS2751	DS2760	DS2761	DS2762	DS2763
DS2770	DS2890	DS28E01	DS29020	DS3903
DS3904	DS3905	DS3930	DS4000	DS4301
DS4510	DS5001	DS5002	DS5240	DS5250
DS7864B	DS7864D	DS80C310	DS80C320	DS80C323
DS80CH11	DS87C520	DS87C550	DSQ3301-K02	

The calculated failure rate for devices using this process is:

FAILURE RATE: MTTF (YRS): 14335 FITS: 8.0

The parameters used to calculate this failure rate are as follows:

Cf: 60% Ea: 0.7 Tu: 25 °C

The reliability data follows. At the start of this data is the process information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available. This report covers data between 4/1/2006 and 3/31/2007 .

Device Information:

Process: 0.6 µm Process
Interconnect: Aluminum / 1% Silicon / 0.5% Copper

Gate Oxide Thickness: 150 Å

OPERATING LIFE

DESCRIPTION	DATE CODE	TEST VEHICLE	CONDITION	READPOINT	QUANTITY	FAILS	FA NO
HIGH TEMP OP LIFE	0612	DS12885	125C, 5.5 VOLTS	1000 HRS	77	0	
HIGH TEMP OP LIFE	0617	DS87C550	125C, 5.5 VOLTS	1000 HRS	45	0	
Total:						0	

STORAGE LIFE

DESCRIPTION	DATE CODE	TEST VEHICLE	CONDITION	READPOINT	QUANTITY	FAILS	FA NO
STORAGE LIFE	0617	DS87C550	150C	1000 HRS	77	0	
Total:						0	

TEMPERATURE CYCLE

DESCRIPTION	DATE CODE	TEST VEHICLE	CONDITION	READPOINT	QUANTITY	FAILS	FA NO
TEMP CYCLE	0612	DS12885	-55C TO 125C	1000 CYS	77	0	
TEMP CYCLE	0617	DS87C550	-55C TO 125C	1000 CYS	77	0	
Total:						0	

TEMPERATURE HUMIDITY BIAS

DESCRIPTION	DATE CODE	TEST VEHICLE	CONDITION	READPOINT	QUANTITY	FAILS	FA NO
HAST	0612	DS12885	130C, 85%R.H.,5.5V	96 HRS	77	0	
BIASED MOISTURE	0617	DS87C550	85/85, 5.5 VOLTS	1000 HRS	77	0	
Total:						0	

UNBIASED MOISTURE RESISTANCE

DESCRIPTION	DATE CODE	TEST VEHICLE	CONDITION	READPOINT	QUANTITY	FAILS	FA NO
AUTOCLAVE	0612	DS12885	121C, 2 ATM STEAM, UNBIASED	168 HRS	77	0	
AUTOCLAVE	0617	DS87C550	121C, 2 ATM STEAM, UNBIASED	168 HRS	77	0	
Total:						0	

FAILURE RATE: MTTF (YRS): 14335 FITS: 8.0